EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L8	52	((leadframe lead adj frame lead$3frame) and lamin$5 and (chip die ic integrated adj circuit) and pack$3).clm.	US-PGPUB	OR	ON	2008/06/06 16:21
S416	4	("20020017718" | "6313529").PN. OR ("6635962").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S415	338	S414 and lead near1 frame and (solder near2 ball bump c4 flip)	USPAT	OR	ON	2008/06/06 12:15
S414	2350	(257/777).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/06/06 12:15
S413	197	(plur$5 multi) near2 (film layer laminat$3) with frame and (IC semiconductor silicon integrated adj circuit chip die wafer)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S412	50	(plur$5 multi) near2 (film layer laminat$3) near2 frame and (IC semiconductor silicon integrated adj circuit chip die wafer)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S411	681	(plur$5 multi) near2 (film layer laminat$3) near2 frame and (IC semiconductor silicon integrated adj circuit chip die wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S410	2329	(plur$5 multi) near2 (film layer laminat$3) with frame and (IC semiconductor silicon integrated adj circuit chip die wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S409	0	"(plur$5multi)near2(filmlayerlaminat$3)withframeand (ICsemiconductorsiliconintegratedadjcircuitchipdiewafer)").PN.	FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/06/06 12:15

S408	3	("6081031" | "6555899" | "6677672").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S407	1	"6734044".pn.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S406	12	S404 and (solder adj contact solder near ball bump c4)	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S405	152	S404 not S399	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S404	157	multi$3layer near2 lead adj frame	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S403	4	("3784948" | "3925801" | "4627151").PN. OR ("6255141").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S402	2	"6255141".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S401	242	S398 or S399	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S400	63	S398 and S399	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S399	162	S397 and 257/67$1.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15

S398	143	S397 and 257/66$1.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S397	1614	laminat$3 with lead adj frame	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S396	142	("3784883" | "4168507" | "4541035" | "4577214" | "4595945" | "4608592" | "4639760" | "4675717" | "4680613" | "4705917").PN. OR ("4891687").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S395	12	("3597834" | "3848077" | "4113981" | "4925024" | "5025114" | "5180888" | "5183969" | "5262226").PN. OR ("5399809").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S394	56	S393 not S389	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S393	81	(IC chip integrated near2 circuit die semiconductor) near3 coated with (titanium it tungsten w gold au) and lead with frame	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S392	28	S390 not S389	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S391	38	S390 not "44"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15

S390	53	(IC chip integrated near2 circuit die semiconductor) near3 coated with (titanium tungsten gold) and lead with frame	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S389	25	(IC chip integrated near2 circuit die semiconductor) near3 coated with (titanium tungsten gold) same lead with frame	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S388	42	(IC chip integrated near2 circuit die semiconductor) near3 coated with (titanium tungsten gold) with lead	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S387	98	S386 and lead near2 frame	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S386	239	S381 and "257"/$.ccls.	USPAT	OR	ON	2008/06/06 12:15
S385	98	S382 and "257"/$.ccls.	USPAT	OR	ON	2008/06/06 12:15
S384	149	S382 and "257"/$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S383	2671	(IC chip integrated near2 circuit die semiconductor) near S379 coated with (titanium tungsten gold) with lead	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15

S382	232	S381 and lead near2 frame	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S381	2671	(IC chip integrated near2 circuit die semiconductor) near S379 coated with (titanium tungsten gold) with lead	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S380	2	S379 and lead near2 frame	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S379	2	"6734044".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S378	2	"5196725".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S377	2	"5229647".pn.	USPAT; DERWENT	OR	ON	2008/06/06 12:15
S376	2	"5196725".pn.	USPAT; DERWENT	OR	ON	2008/06/06 12:15
S375	2	"5191725".pn.	USPAT; DERWENT	OR	ON	2008/06/06 12:15
S374	1	1992-386699.NRAN.	DERWENT	OR	ON	2008/06/06 12:15
S373	9	(US-5777265-$ or US-5734198-$ or US-5399809-$ or US-5864173-$ or US-5214845-$ or US-4891687-$ or US-5389816-$).did. or (US-5777265-$ or JP-04286148-$).did.	USPAT; DERWENT	OR	ON	2008/06/06 12:15

S372	37	("4445271" | "4835120" | "4891687" | "5032895" | "5053921" | "5089878" | "5089881").PN. OR ("5220195").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S371	6	("4891687" | "5089878" | "5196725" | "5214845" | "5220195" | "5237202").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S370	9	("4891687" | "5089878" | "5196725" | "5214845" | "5220195" | "5237202").PN. OR ("5389816").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S369	26	(Multi near2 layer with lead near2 frame).ti. and "257"/$.ccls.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S368	25	("4320438" | "4839717" | "4879588" | "4891687" | "4972253" | "4980034" | "5008734" | "5012386" | "5158912" | "5235209" | "5235211" | "5258575" | "5264729" | "5272590" | "5311057" | "5331511").PN. OR ("5777265").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S367	10	("5,196,725", "5,237,202", "5,399,809", "5,734,198" "5,777,265").pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S366	483	S365 and (multi near2 layer multilayer laminate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S365	4648	(257/666).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/06/06 12:15
S364	3	("6081031" | "6555899" | "6677672").PN. OR ("6734044").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S363	2	"6734044".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S362	3	("6081031" | "6555899" | "6677672").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S361	1	"6734044".pn.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15

S360	12	S358 and (solder adj contact solder near ball bump c4)	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S359	152	S358 not S353	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S358	157	multi$3layer near2 lead adj frame	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S357	4	("3784948" | "3925801" | "4627151").PN. OR ("6255141").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S356	2	"6255141".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S355	242	S352 or S353	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S354	63	S352 and S353	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S353	162	S351 and 257/67$1.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S352	143	S351 and 257/66$1.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15

S351	1614	laminat$3 with lead adj frame	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S350	142	("3784883" | "4168507" | "4541035" | "4577214" | "4595945" | "4608592" | "4639760" | "4675717" | "4680613" | "4705917").PN. OR ("4891687").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S349	12	("3597834" | "3848077" | "4113981" | "4925024" | "5025114" | "5180888" | "5183969" | "5262226").PN. OR ("5399809").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S348	56	S347 not S343	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S347	81	(I C chip integrated near2 circuit die semiconductor) near3 coated with (titanium it tungsten w gold au) and lead with frame	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S346	28	S344 not S343	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S345	38	S344 not "44"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S344	53	(I C chip integrated near2 circuit die semiconductor) near3 coated with (titanium tungsten gold) and lead with frame	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15

S343	25	(IC chip integrated near2 circuit die semiconductor) near3 coated with (titanium tungsten gold) same lead with frame	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S342	42	(IC chip integrated near2 circuit die semiconductor) near3 coated with (titanium tungsten gold) with lead	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S341	98	S340 and lead near2 frame	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S340	239	S335 and "257"/$.ccls.	USPAT	OR	ON	2008/06/06 12:15
S339	98	S337 and "257"/$.ccls.	USPAT	OR	ON	2008/06/06 12:15
S338	149	S337 and "257"/$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S337	232	S335 and lead near2 frame	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S336	2	S334 and lead near2 frame	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15

S335	2671	(IC chip integrated near2 circuit die semiconductor) near S334 coated with (titanium tungsten gold) with lead	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S334	2	"6734044".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S333	2	"5196725".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S332	2	"5229647".pn.	USPAT; DERWENT	OR	ON	2008/06/06 12:15
S331	2	"5196725".pn.	USPAT; DERWENT	OR	ON	2008/06/06 12:15
S330	2	"5191725".pn.	USPAT; DERWENT	OR	ON	2008/06/06 12:15
S329	1	1992-386699.NRAN.	DERWENT	OR	ON	2008/06/06 12:15
S328	9	(US-5777265-$ or US-5734198-$ or US-5399809-$ or US-5864173-$ or US-5214845-$ or US-4891687-$ or US-5389816-$).did. or (US-5777265-$ or JP-04286148-$).did.	USPAT; DERWENT	OR	ON	2008/06/06 12:15
S327	37	("4445271" | "4835120" | "4891687" | "5032895" | "5053921" | "5089878" | "5089881").PN. OR ("5220195").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S326	6	("4891687" | "5089878" | "5196725" | "5214845" | "5220195" | "5237202").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S325	9	("4891687" | "5089878" | "5196725" | "5214845" | "5220195" | "5237202").PN. OR ("5389816").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S324	26	(Multi near2 layer with lead near2 frame).ti. and "257"/$.ccls.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S323	25	("4320438" | "4839717" | "4879588" | "4891687" | "4972253" | "4980034" | "5008734" | "5012386" | "5158912" | "5235209" | "5235211" | "5258575" | "5264729" | "5272590" | "5311057" | "5331511").PN. OR ("5777265").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15

S322	10	("5,196,725", "5,237,202", "5,399,809", "5,734,198" "5,777,265").pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S321	483	S320 and (multi near2 layer multilayer laminate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S320	4648	(257/666).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/06/06 12:15
S319	3	("6081031" | "6555899" | "6677672").PN. OR ("6734044").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S318	2	"6734044".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S317	18	("5578525" | "5580795" | "5909058" | "6188127" | "6204562" | "6287892" | "6324067" | "6350954").PN. OR ("6548330").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S316	13	("3908185" | "4866571" | "5057376" | "5404273" | "5689091" | "5801446" | "5847936" | "5936305" | "6011692").PN. OR ("6350954").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S315	172	S314 and cavity	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S314	578	S312 and S313	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S313	662	(lead near1 frame or leadframe) with (multilayer$3 or multi near1 layer$3)	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S312	20630	(lead near1 frame or leadframe).bstx.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S311	17	("20020020907" | "20020031856" | "5243498" | "5629563" | "6143981" | "6236109" | "6284570" | "6369454" | "6458617" | "6507098").PN. OR ("6677672").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15

S310	3	("6081031" | "6555899" | "6677672").PN. OR ("6734044").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S309	3	("6081031" | "6555899" | "6677672").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S308	3	("6081031" | "6555899" | "6677672").PN. OR ("6734044").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S307	4	("20020017718" | "6313529").PN. OR ("6635962").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S306	338	S305 and lead near1 frame and (solder near2 ball bump c4 flip)	USPAT	OR	ON	2008/06/06 12:15
S305	2350	(257/777).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/06/06 12:15
S304	197	(plur$5 multi) near2 (film layer laminat$3) with frame and (IC semiconductor silicon integrated adj circuit chip die wafer)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S303	50	(plur$5 multi) near2 (film layer laminat$3) near2 frame and (IC semiconductor silicon integrated adj circuit chip die wafer)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S302	681	(plur$5 multi) near2 (film layer laminat$3) near2 frame and (IC semiconductor silicon integrated adj circuit chip die wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S301	2329	(plur$5 multi) near2 (film layer laminat$3) with frame and (IC semiconductor silicon integrated adj circuit chip die wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S300	0	("(plur$5multi)near2(filmlayerlaminat$3)withframeand (ICsemiconductorsiliconintegratedadjcircuitchipdiewafer)").PN.	FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/06/06 12:15
S299	3	("6081031" | "6555899" | "6677672").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15

S298	1	"6734044".pn.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S297	12	S295 and (solder adj contact solder near ball bump c4)	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S296	152	S295 not S290	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S295	157	multi$3layer near2 lead adj frame	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S294	4	("3784948" | "3925801" | "4627151").PN. OR ("6255141").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S293	2	"6255141".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S292	242	S289 or S290	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S291	63	S289 and S290	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S290	162	S288 and 257/67$1.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S289	143	S288 and 257/66$1.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15

S288	1614	laminat$3 with lead adj frame	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S287	142	("3784883" | "4168507" | "4541035" | "4577214" | "4595945" | "4608592" | "4639760" | "4675717" | "4680613" | "4705917").PN. OR ("4891687").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S286	12	("3597834" | "3848077" | "4113981" | "4925024" | "5025114" | "5180888" | "5183969" | "5262226").PN. OR ("5399809").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S285	56	S284 not S280	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S284	81	(IC chip integrated near2 circuit die semiconductor) near3 coated with (titanium it tungsten w gold au) and lead with frame	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S283	28	S281 not S280	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S282	38	S281 not "44"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S281	53	(IC chip integrated near2 circuit die semiconductor) near3 coated with (titanium tungsten gold) and lead with frame	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15

S280	25	(IC chip integrated near2 circuit die semiconductor) near3 coated with (titanium tungsten gold) same lead with frame	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S279	42	(IC chip integrated near2 circuit die semiconductor) near3 coated with (titanium tungsten gold) with lead	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S278	98	S277 and lead near2 frame	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S277	239	S272 and "257"/$.ccls.	USPAT	OR	ON	2008/06/06 12:15
S276	98	S273 and "257"/$.ccls.	USPAT	OR	ON	2008/06/06 12:15
S275	149	S273 and "257"/$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S274	2671	(IC chip integrated near2 circuit die semiconductor) near S270 coated with (titanium tungsten gold) with lead	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S273	232	S272 and lead near2 frame	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15

S272	2671	(I C chip integrated near2 circuit die semiconductor) near S270 coated with (titanium tungsten gold) with lead	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S271	2	S270 and lead near2 frame	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S270	2	"6734044".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S269	2	"5196725".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S268	2	"5229647".pn.	USPAT; DERWENT	OR	ON	2008/06/06 12:15
S267	2	"5196725".pn.	USPAT; DERWENT	OR	ON	2008/06/06 12:15
S266	2	"5191725".pn.	USPAT; DERWENT	OR	ON	2008/06/06 12:15
S265	1	1992-386699.NRAN.	DERWENT	OR	ON	2008/06/06 12:15
S264	9	(US-5777265-$ or US-5734198-$ or US-5399809-$ or US-5864173-$ or US-5214845-$ or US-4891687-$ or US-5389816-$).did. or (US-5777265-$ or JP-04286148-$).did.	USPAT; DERWENT	OR	ON	2008/06/06 12:15
S263	37	("4445271" | "4835120" | "4891687" | "5032895" | "5053921" | "5089878" | "5089881").PN. OR ("5220195").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S262	6	("4891687" | "5089878" | "5196725" | "5214845" | "5220195" | "5237202").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S261	9	("4891687" | "5089878" | "5196725" | "5214845" | "5220195" | "5237202").PN. OR ("5389816").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15

S260	26	(Multi near2 layer with lead near2 frame).ti. and "257"/$.ccls.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S259	25	("4320438" | "4839717" | "4879588" | "4891687" | "4972253" | "4980034" | "5008734" | "5012386" | "5158912" | "5235209" | "5235211" | "5258575" | "5264729" | "5272590" | "5311057" | "5331511").PN. OR ("5777265").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S258	10	("5,196,725", "5,237,202", "5,399,809", "5,734,198" "5,777,265").pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S257	483	S256 and (multi near2 layer multilayer laminate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S256	4648	(257/666).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/06/06 12:15
S255	3	("6081031" | "6555899" | "6677672").PN. OR ("6734044").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S254	2	"6734044".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S253	3	("6081031" | "6555899" | "6677672").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S252	1	"6734044".pn.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S251	12	S249 and (solder adj contact solder near ball bump c4)	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S250	152	S249 not S244	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S249	157	multi$3layer near2 lead adj frame	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15

S248	4	("3784948" | "3925801" | "4627151").PN. OR ("6255141").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S247	2	"6255141".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S246	242	S243 or S244	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S245	63	S243 and S244	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S244	162	S242 and 257/67$1.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S243	143	S242 and 257/66$1.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S242	1614	laminat$3 with lead adj frame	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S241	142	("3784883" | "4168507" | "4541035" | "4577214" | "4595945" | "4608592" | "4639760" | "4675717" | "4680613" | "4705917").PN. OR ("4891687").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S240	12	("3597834" | "3848077" | "4113981" | "4925024" | "5025114" | "5180888" | "5183969" | "5262226").PN. OR ("5399809").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15

S239	56	S238 not S234	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S238	81	(IC chip integrated near2 circuit die semiconductor) near3 coated with (titanium it tungsten w gold au) and lead with frame	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S237	28	S235 not S234	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S236	38	S235 not "44"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S235	53	(IC chip integrated near2 circuit die semiconductor) near3 coated with (titanium tungsten gold) and lead with frame	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S234	25	(IC chip integrated near2 circuit die semiconductor) near3 coated with (titanium tungsten gold) same lead with frame	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S233	42	(IC chip integrated near2 circuit die semiconductor) near3 coated with (titanium tungsten gold) with lead	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15

S232	98	S231 and lead near2 frame	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S231	239	S226 and "257"/$.ccls.	USPAT	OR	ON	2008/06/06 12:15
S230	98	S228 and "257"/$.ccls.	USPAT	OR	ON	2008/06/06 12:15
S229	149	S228 and "257"/$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S228	232	S226 and lead near2 frame	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S227	2	S225 and lead near2 frame	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S226	2671	(IC chip integrated near2 circuit die semiconductor) near S225 coated with (titanium tungsten gold) with lead	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S225	2	"6734044".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15

S224	2	"5196725".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S223	2	"5229647".pn.	USPAT; DERWENT	OR	ON	2008/06/06 12:15
S222	2	"5196725".pn.	USPAT; DERWENT	OR	ON	2008/06/06 12:15
S221	2	"5191725".pn.	USPAT; DERWENT	OR	ON	2008/06/06 12:15
S220	1	1992-386699.NRAN.	DERWENT	OR	ON	2008/06/06 12:15
S219	9	(US-5777265-$ or US-5734198-$ or US-5399809-$ or US-5864173-$ or US-5214845-$ or US-4891687-$ or US-5389816-$).did. or (US-5777265-$ or JP-04286148-$).did.	USPAT; DERWENT	OR	ON	2008/06/06 12:15
S218	37	("4445271" | "4835120" | "4891687" | "5032895" | "5053921" | "5089878" | "5089881").PN. OR ("5220195").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S217	6	("4891687" | "5089878" | "5196725" | "5214845" | "5220195" | "5237202").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S216	9	("4891687" | "5089878" | "5196725" | "5214845" | "5220195" | "5237202").PN. OR ("5389816").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S215	26	(Multi near2 layer with lead near2 frame).ti. and "257"/$.ccls.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S214	25	("4320438" | "4839717" | "4879588" | "4891687" | "4972253" | "4980034" | "5008734" | "5012386" | "5158912" | "5235209" | "5235211" | "5258575" | "5264729" | "5272590" | "5311057" | "5331511").PN. OR ("5777265").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S213	10	("5,196,725", "5,237,202", "5,399,809", "5,734,198" "5,777,265").pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15
S212	483	S211 and (multi near2 layer multilayer laminate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15

S211	4648	(257/666).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/06/06 12:15
S210	3	("6081031" | "6555899" | "6677672").PN. OR ("6734044").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/06/06 12:15
S209	2	"6734044".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/06 12:15

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